

Silicon NPN Power Transistors

2SC3231

DESCRIPTION

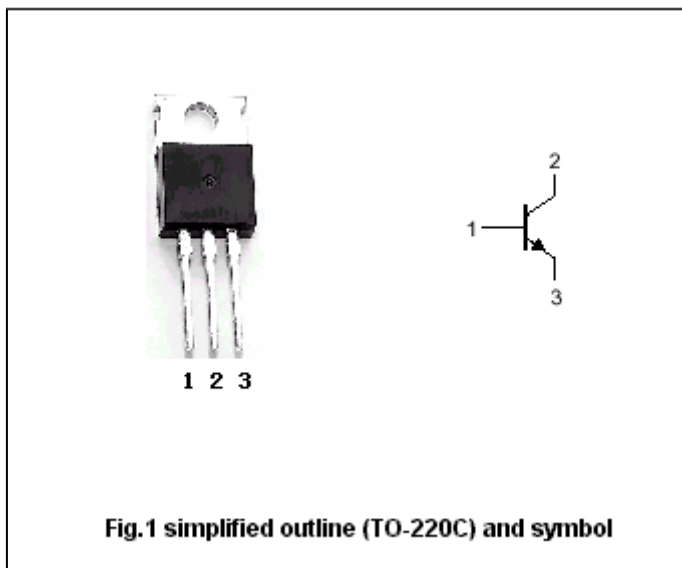
- With TO-220 package
- Wide area of safe operation

APPLICATIONS

- Switching regulators
- General purpose power amplifiers
- TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		4	A
P _C	Collector power dissipation	T _C =25°C	40	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC3231

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	30		150	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		8		MHz

Silicon NPN Power Transistors

2SC3231

PACKAGE OUTLINE

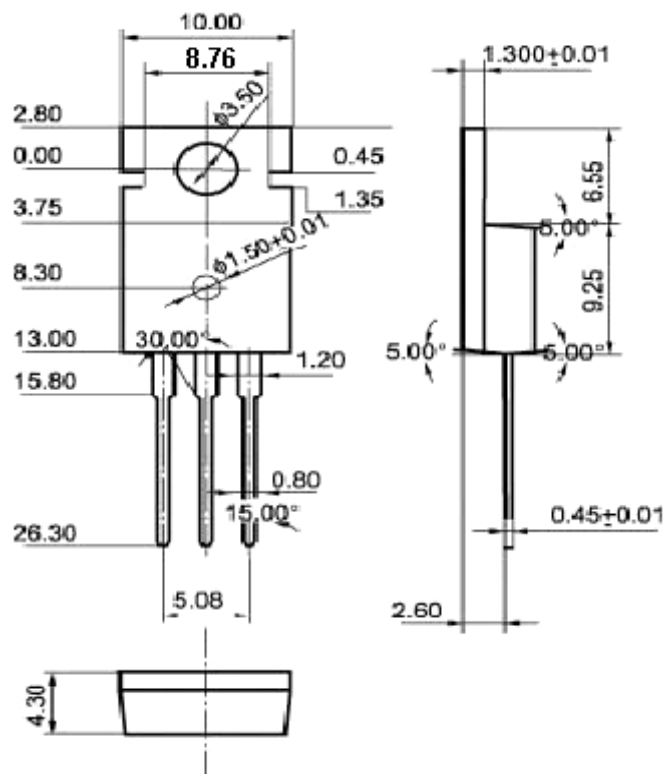


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)